

isc Silicon NPN Power Transistor**2SD608****DESCRIPTION**

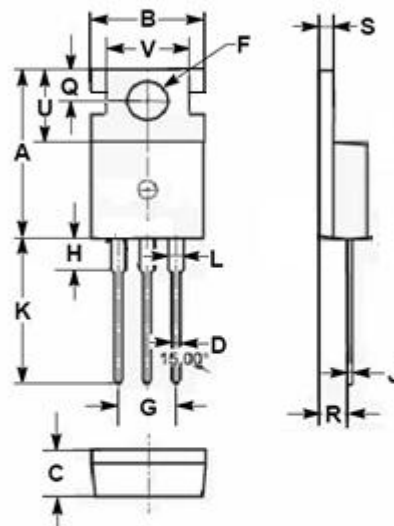
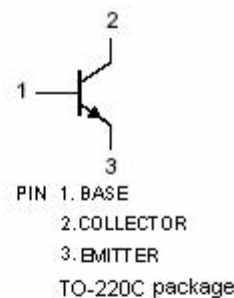
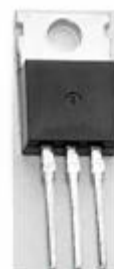
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 160V(\text{Min})$
- Complement to Type 2SB628
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio frequency power amplifier and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 160 | V |
| V_{CEO} | Collector-Emitter Voltage | 160 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 1.5 | A |
| I_{CM} | Collector Current-Peak | 3.0 | A |
| I_B | Base Current-Continuous | 0.3 | A |
| P_C | Collector Power Dissipation @ $T_a=25^\circ\text{C}$ | 1.5 | W |
| | Collector Power Dissipation @ $T_c=25^\circ\text{C}$ | 20 | |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |



| DIM | mm | |
|-----|-------|-------|
| | MIN | MAX |
| A | 15.50 | 15.90 |
| B | 9.80 | 10.20 |
| C | 4.20 | 4.50 |
| D | 0.70 | 0.90 |
| F | 3.40 | 3.70 |
| G | 4.98 | 5.18 |
| H | 2.68 | 2.90 |
| J | 0.44 | 0.60 |
| K | 12.80 | 13.40 |
| L | 1.20 | 1.45 |
| Q | 2.70 | 2.90 |
| R | 2.30 | 2.70 |
| S | 1.29 | 1.35 |
| U | 6.45 | 6.65 |
| V | 8.66 | 8.86 |

isc Silicon NPN Power Transistor**2SD608****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 1A; I _B = 0.1A | | 0.5 | 2.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 1A; I _B = 0.1A | | 0.9 | 1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 120V; I _E = 0 | | | 1.0 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 3V; I _C = 0 | | | 1.0 | μ A |
| h _{FE-1} | DC Current Gain | I _C = 5mA; V _{CE} = 5V | 25 | 40 | | |
| h _{FE-2} | DC Current Gain | I _C = 0.3A; V _{CE} = 5V | 40 | 80 | 200 | |
| C _{OB} | Collector Output Capacitance | I _E = 0; V _{CB} = 10V; f= 1MHz | | 25 | | pF |
| f _T | Current-Gain—Bandwidth Product | I _C = 0.1A; V _{CE} = 5V | | 45 | | MHz |

◆ h_{FE-2} Classifications

| S | R | Q |
|-------|--------|---------|
| 40-80 | 60-120 | 100-200 |

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